

**METALLOPORPHYRINS BASED
SEMICONDUCTING THIN FILMS DEPOSITION
AND CHARACTERIZATION FOR
ORGANIC FIELD EFFECT TRANSISTOR**

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**METALLOPORPHYRINS BASED SEMICONDUCTING THIN FILMS
DEPOSITION AND CHARACTERIZATION FOR
ORGANIC FIELD EFFECT TRANSISTOR**

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LIST ABBREVIATIONS

| | |
|-----------|---|
| OFET | Organic Field effect Transistor |
| OTFT | Organic Thin Film Transistor |
| MOSFET | Metal-oxide-semiconductor field-effect transistor |
| OEP | Octaethyl–21H, 23H–Porphine |
| OEP-Cu | Octaethyl–21H, 23H–Porphine Copper (II) |
| OEP-Ni | Octaethyl–21H, 23H–Porphine Nickel (II) |
| OEP-Zn | Octaethyl–21H, 23H–Porphine Zinc (II) |
| Proto-Zn | Protoporphyrin IX Zinc (II) |
| Proto-Co | Protoporphyrin IX Cobalt Chloride |
| AOEP | Annealed Octaethyl–21H, 23H–Porphine |
| AOEP-Cu | Annealed Octaethyl–21H, 23H–Porphine Copper (II) |
| AOEP-Ni | Annealed Octaethyl–21H, 23H–Porphine Nickel (II) |
| AOEP-Zn | Annealed Octaethyl–21H, 23H–Porphine Zinc (II) |
| AProto-Zn | Annealed Protoporphyrin IX Zinc (II) |
| AProto-Co | Annealed Protoporphyrin IX Cobalt Chloride |
| BCB | Benzocyclobutene |
| ITO | Indium Tin Oxide |
| i.e | Id est /that is |
| vs | Versus |
| Ag | Silver |
| Au | Gold |

| | |
|------------------|-------------------------------------|
| Cu | Copper |
| Al | Aluminium |
| Pt | Platinum |
| Ge | Germanium |
| Si | Silicon |
| GaAs | Gallium arsenide |
| GaP | Gallium phosphide |
| HOMO | Highest occupied molecular orbital |
| LUMO | Lowest unoccupied molecular orbital |
| TCNQ | Tetracyanoquinodimethane |
| P3HT | Poly(3-hexylthiophene) |
| PPV | Poly(p-phenylenevinylene) |
| PFO | Polyfluorene |
| P3AT | Poly(3-alkylthiophene) |
| CuPc | Cu-phthalocyanine |
| C ₆₀ | Fullerene |
| Alq ₃ | tris(8-hydroxyquinolinato)aluminium |
| PC | Polycarbonate |
| PP | Polypropylene |
| PET | Polyethylene terephthalate |
| PVDF | Polyvinylidene fluoride |
| PEN | Polyethylene naphthalate |
| PPS | Polyphenylene sulphide |